

## **AMENDMENTS TO THE CLAIMS**

A listing of all claims and their current status in accordance with 37 C.F.R. § 1.121(c) is provided below.

1-21. (Canceled)

22. (Original) A memory module comprising:

a substrate; and

a plurality of memory devices coupled to the substrate, wherein each of the plurality of memory devices comprises a respective plurality of programmable elements and wherein a respective operating current value for each of the plurality of memory devices are stored in the respective plurality of programmable elements.

23. (Original) The memory module, as set forth in claim 22, comprising a non-volatile memory device coupled to the substrate, wherein a respective operating current value for each of the plurality of memory devices are stored in the non-volatile memory device.

24. (Original) The memory module, as set forth in claim 23, wherein the non-volatile memory device comprises a serial presence detect device.

25. (Original) The memory module, as set forth in claim 22, wherein the memory module comprises a dual inline memory module.

26. (Original) The memory module, as set forth in claim 22, wherein each of the plurality of memory devices comprises a dynamic random access memory device.

27. (Original) The memory module, as set forth in claim 22, wherein each of the plurality of programmable elements comprises an antifuse.

28. (Original) A system comprising:

- a processor; and
- a memory module coupled to the processor and comprising:
  - a substrate; and
  - a plurality of memory devices coupled to the substrate, wherein each of the plurality of memory devices comprises a respective plurality of programmable elements and wherein a respective operating current value for each of the plurality of memory devices are stored in the respective plurality of programmable elements.

29. (Original) The system, as set forth in claim 28, comprising a non-volatile memory device coupled to the substrate, wherein a respective operating current value for each of the plurality of memory devices are stored in the non-volatile memory device.

30. (Original) The system, as set forth in claim 29, wherein the non-volatile memory device comprises a serial presence detect device.

31. (Original) The system, as set forth in claim 28, wherein the memory module comprises a dual inline memory module.
32. (Original) The system, as set forth in claim 28, wherein each of the plurality of memory devices comprises a dynamic random access memory device.
33. (Original) The system, as set forth in claim 28, wherein each of the plurality of programmable elements comprises an antifuse.